

# **isc Silicon PNP Power Transistor**

# **BD828**

#### DESCRIPTION

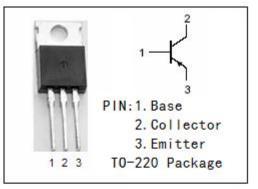
- Collector-Emitter Breakdown Voltage-: V<sub>(BR)CEO</sub>= -60V(Min)
- High DC Current Gain
- Low Saturation Voltage
- Complement to Type BD827
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

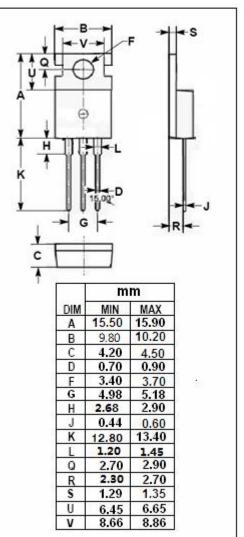
#### APPLICATIONS

 Designed for driver-stages in hi-fi amplifiers and television circuits.

ABSOLUTE MAXIMUM RATINGS(Ta=25°C)									
SYMBOL	PARAMETER	TER VALUE		UNIT					
Vсво	Collector-Base Voltage		-60	v					
V <sub>CEO</sub>	Collector-Emitter Voltage		-60	V					
V <sub>EBO</sub>	Emitter-Base Voltage	ie -5		V					
lc	Collector Current-Continuous	-1.0		А					
I <sub>CP</sub>	Collector Current-Peak	-1.5		А					
Pc	Collector Power Dissipation @ Ta=25°C	2 10		W					
	Collector Power Dissipation @ $T_c=25^{\circ}C$								
TJ	Junction Temperature	150		°C					
T <sub>stg</sub>	Storage Temperature Range	-65~150		°C					
THERMAL CHARACTERISTICS									
SYMBOL	PARAMETER		МАХ	UNIT					
R <sub>th j-c</sub>	Thermal Resistance, Junction to Case		12.5	°C/W					
R <sub>th j-a</sub>	Thermal Resistance, Junction to Ambient		62.5	°C/W					

## ABSOLUTE MAXIMUM RATINGS(Ta=25℃)







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### **ELECTRICAL CHARACTERISTICS**

#### $T_c=25^{\circ}C$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	МАХ	UNIT
Vceo(sus)	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = -30mA; I <sub>B</sub> = 0	-60			V
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> =- 500mA; I <sub>B</sub> = -50mA			-0.5	V
V <sub>BE(on)</sub>	Base-Emitter On Voltage	I <sub>C</sub> = -0.5A ; V <sub>CE</sub> = -2V			-1.0	V
Ісво	Collector Cutoff Current	V <sub>CB</sub> = -30V; I <sub>E</sub> = 0			-0.1	uA
		V <sub>св</sub> =-30V; I <sub>Е</sub> = 0; Т <sub>с</sub> = 125℃			-10	
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = -5V; I <sub>C</sub> = 0			-10	uA
h <sub>FE-1</sub>	DC Current Gain	I <sub>C</sub> = -5mA ; V <sub>CE</sub> = -2V	25			
h <sub>FE-2</sub>	DC Current Gain	I <sub>C</sub> = -150mA ; V <sub>CE</sub> = -2V	40		250	
h <sub>FE-3</sub>	DC Current Gain	I <sub>C</sub> = -500mA ; V <sub>CE</sub> =- 2V	25			
f⊤	Current-Gain—Bandwidth Product	I <sub>C</sub> = -50mA ; V <sub>CE</sub> =- 5V		75		MHz

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